AMENDMENTS TO THE CLAIMS

1-22. (cancelled)

23. (previously presented): A light emitting diode, comprising at least:

a substrate;

a reflective layer formed over the substrate;

a first reaction layer formed over said reflective layer;

a transparent adhesive layer formed over said first reaction layer;

a second reaction layer formed over said transparent adhesive layer;

and an LED stack formed over said second reaction layer;

wherein each of the first and second reaction layers is formed to enhance an adhesion provided by the transparent adhesive layer;

wherein said transparent adhesive layer comprises at least a material selected from the group consisting of polyimide (PI), benzocyclobutene (BCB), and perfluorocyclobutane (PFCB); and

wherein each said first and second reaction layers comprises at least a material selected from the group consisting of SiNx, Ti, and Cr.

24. (previously presented): A light emitting diode according to claim 23, further comprising a transparent conductive layer between said second reaction layer and said LED stack.

25. (previously presented): A light emitting diode according to claim 23, wherein said reflective layer is a reflective metal layer.

26. (cancelled)

27. (previously presented): A light emitting diode according to claim 25, wherein said reflective metal layer comprises at least a material selected from the group consisting of In, Sn, Al, Au, Pt, Zn, Ag, Ti, Pb, Pd, Ge, Cu, AuBe, AuGe, Ni, PbSn, and AuZn.

28-43. (cancelled)

44. (previously presented): A light emitting diode, comprising at least:

a reflective means;

a first reaction layer formed over said reflective means;

a transparent adhesive layer formed over said first reaction layer;

a second reaction layer formed over said transparent adhesive layer; and

an LED stack formed over said second reaction layer;

wherein the first and second reaction layers enhance adhesion provided by the transparent adhesive layer,

wherein said transparent adhesive layer comprises at least a material selected from the group consisting of polyimide (PI), benzocyclobutene (BCB), and perfluorocyclobutane (PFCB); and

wherein each said first and second reaction layers comprises at least a material selected from the group consisting of SiNx, Ti, and Cr.

45. (previously presented): A light emitting diode, comprising at least:

a substrate;

a reflective layer disposed on the substrate;

a first reaction layer formed on said reflective layer;

a transparent adhesive layer formed directly on said first reaction layer, said first reaction layer adhering to the transparent adhesive layer;

a second reaction layer formed directly on said transparent adhesive layer, said second reaction layer adhering to the transparent adhesive layer; and

an LED stack formed over said second reaction layer,

wherein said transparent adhesive layer comprises at least a material selected from the group consisting of polyimide (PI), benzocyclobutene (BCB), and perfluorocyclobutane (PFCB); and

wherein each said first and second reaction layers comprises at least a material selected from the group consisting of SiNx, Ti, and Cr.

46. (cancelled)

47. (previously presented): A light emitting diode according to claim 45, further comprising a transparent conductive layer between said second reaction layer and said LED stack.

48. (previously presented): A light emitting diode according to claim 45, wherein said reflective layer is a reflective metal layer.

49. (previously presented): A light emitting diode according to claim 48, wherein said reflective metal layer comprises at least a material selected from the group consisting of In, Sn, Al, Au, Pt, Zn, Ag, Ti, Pb, Pd, Ge, Cu, AuBe, AuGe, Ni, PbSn, and AuZn.

50-51. (cancelled)

52 (new): A light emitting diode according to claim 23, wherein said reflective layer is a reflective oxide layer.

53 (new): A light emitting diode according to claim 52, wherein said reflective oxide layer comprises at least a material selected from the group consisting of SiNx, SiO_2, Al2O3, TiO2, and MgO.